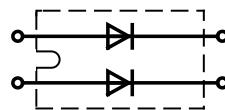


# Fast Recovery Epitaxial Diode (FRED)

$I_{FAVM} = 2 \times 91 \text{ A}$   
 $V_{RRM} = 1200 \text{ V}$   
 $t_{rr} = 40 \text{ ns}$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
1200	1200	DSEI 2x 101-12A



miniBLOC, SOT-227 B



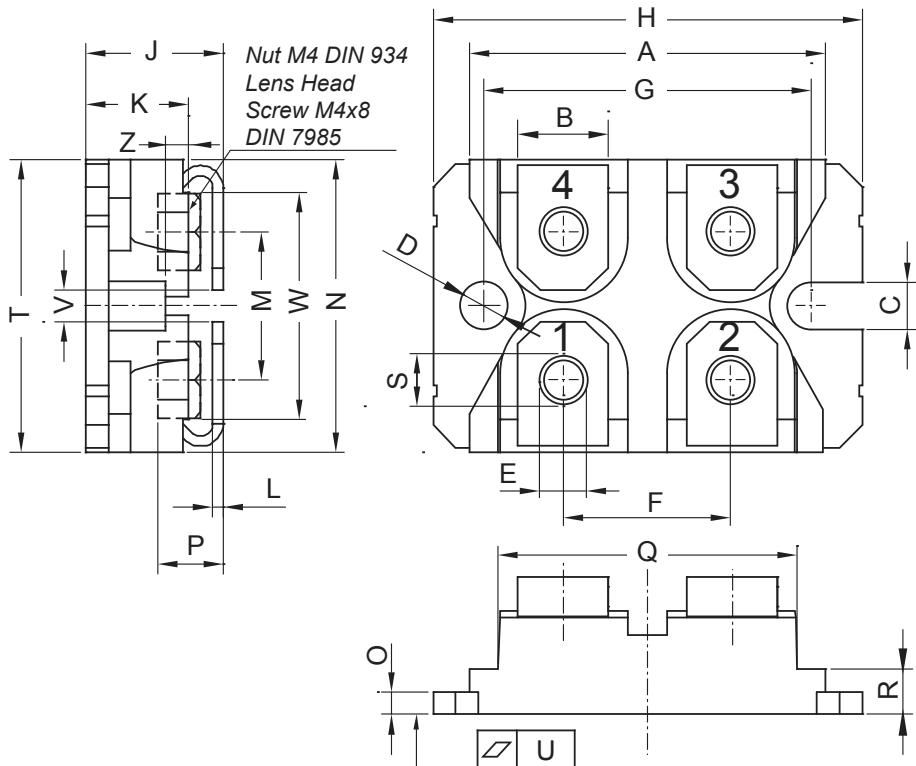
E72873

Symbol	Test Conditions	Maximum Ratings (per diode)	
$I_{FRMS}$	$T_{VJ} = T_{VJM}$	130	A
$I_{F(AV)M}^{\circledast}$	$T_c = 50^\circ\text{C}$ ; rectangular, $d = 0.5$	91	A
$I_{FRM}$	$t_p < 10 \mu\text{s}$ ; rep. rating, pulse width limited by $T_{VJM}$	TBD	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine	900	A
	$t = 8.3 \text{ ms}$ (60 Hz), sine	970	A
	$T_{VJ} = 150^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine	810	A
	$t = 8.3 \text{ ms}$ (60 Hz), sine	870	A
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	4100	$\text{A}^2\text{s}$
	$t = 8.3 \text{ ms}$ (60 Hz), sine	4000	$\text{A}^2\text{s}$
	$T_{VJ} = 150^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine	3300	$\text{A}^2\text{s}$
	$t = 8.3 \text{ ms}$ (60 Hz), sine	3200	$\text{A}^2\text{s}$
$T_{VJ}$		-40...+150	$^\circ\text{C}$
$T_{VJM}$		150	$^\circ\text{C}$
$T_{stg}$		-40...+150	$^\circ\text{C}$
$P_{tot}$	$T_c = 25^\circ\text{C}$	250	W
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
$M_d$	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

Symbol	Test Conditions	Characteristic Values (per diode)	
		typ.	max.
$I_R$	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$	3	mA
	$T_{VJ} = 25^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$	1.5	mA
	$T_{VJ} = 125^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$	15	mA
$V_F$	$I_F = 100 \text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$	1.61	V
	$T_{VJ} = 25^\circ\text{C}$	1.87	V
$V_{TO}$	For power-loss calculations only	1.01	V
$r_T$		6.1	$\text{m}\Omega$
$R_{thJC}$		0.5	K/W
$R_{thCH}$			K/W
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-\text{di}/\text{dt} = 400 \text{ A}/\mu\text{s}$ ; $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	40	60
			ns
$I_{RM}$	$V_R = 100 \text{ V}$ ; $I_F = 75 \text{ A}$ ; $-\text{di}_F/\text{dt} = 200 \text{ A}/\mu\text{s}$ $L \leq 0.05 \text{ mH}$ ; $T_{VJ} = 100^\circ\text{C}$	24	30
			A

<sup>①</sup>  $I_{FAVM}$  rating includes reverse blocking losses at  $T_{VJM}$ ,  $V_R = 0.8 V_{RRM}$ , duty cycle  $d = 0.5$   
Data according to IEC 60747

## miniBLOC, SOT-227 B



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

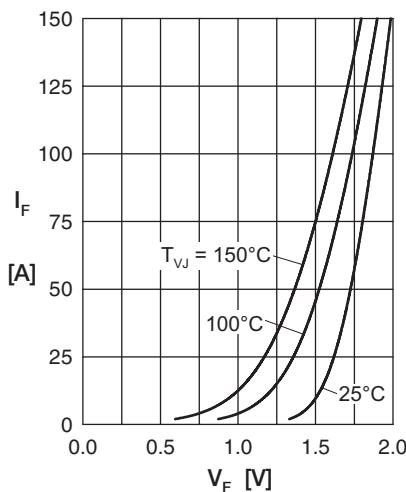
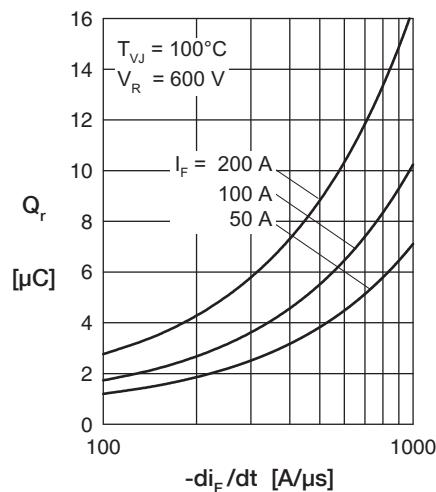
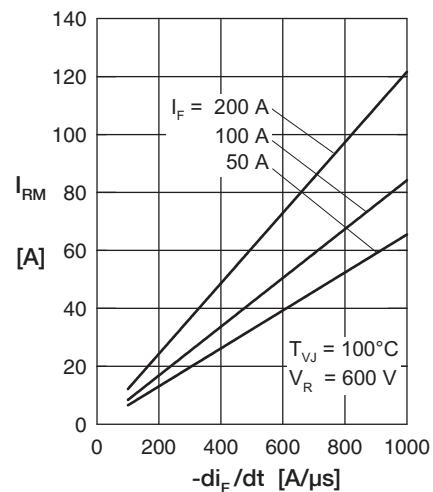
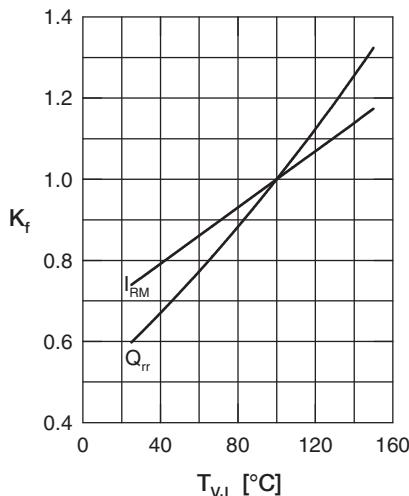
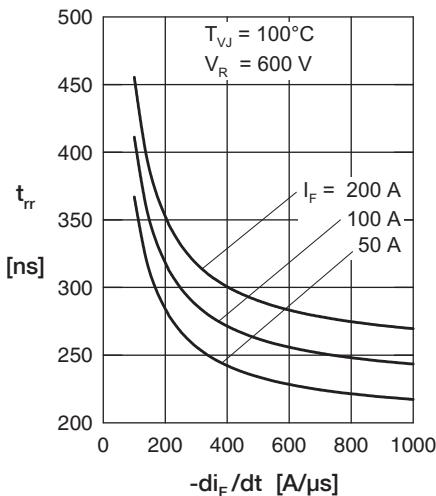
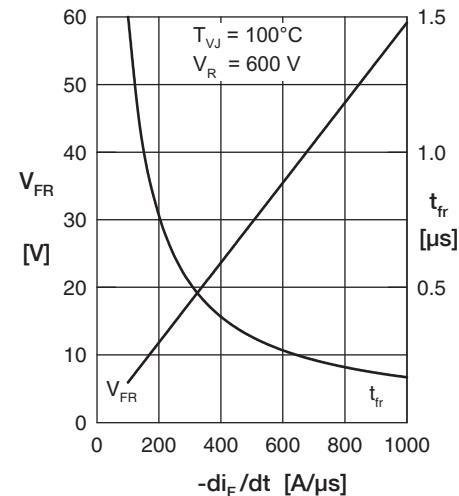
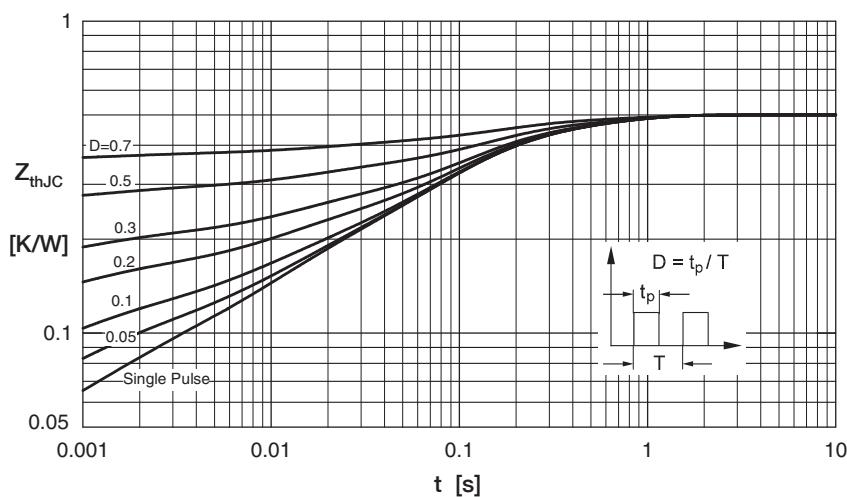
Fig. 1 Forward current  $I_F$  versus  $V_F$ Fig. 2 Typ. reverse recov. charge  $Q_r$  versus  $-di_F/dt$ Fig. 3 Typ. peak reverse current  $I_{rr}$  versus  $-di_F/dt$ Fig. 4 Dyn. parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$ Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$ Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$ 

Fig. 7 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ [K/W]	$t_i$ [s]
1	0.0020	0.00002
2	0.0050	0.00081
3	0.0076	0.01
4	0.0240	0.94
5	0.0114	0.45